

# TECHNICAL DATA SHEET

6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803

Website: http://www.microsemi.com

## PNP POWER SILICON TRANSISTOR

 ${\it Qualified per MIL-PRF-19500/545}$ 

### **ELECTRICAL CHARACTERISTICS**

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
ON CHARACTERTICS					•
Forward-Current Transfer Ratio					
$I_C = 50 \text{mAdc}, V_{CE} = 5 \text{Vdc}$	2N5151 2N5153		20 50		
$I_C = 2.5 Adc$ , $V_{CE} = 5 Vdc$	2N5151 2N5153	$h_{ m FE}$	30 70	90 200	
$I_C = 5 Adc, V_{CE} = 5 Vdc$	2N5151 2N5153		20 40		
Collector-Emitter Saturation Voltage					
$\begin{split} &I_C=2.5\text{Adc},I_B=250\text{mAdc}\\ &I_C=5.0\text{Adc},I_B=500\text{mAdc} \end{split}$		V <sub>CE(sat)</sub>		0.75 1.5	Vdc
Base-Emitter Voltage Non-Saturation $I_C = 2.5 Adc, V_{CE} = 5 Vdc$		$V_{ m BE}$		1.45	Vdc
Base-Emitter Saturation Voltage					
$\begin{split} &I_C=2.5\text{Adc},I_B=250\text{mAdc}\\ &I_C=5.0\text{Adc},I_B=500\text{mAdc} \end{split}$		V <sub>BE(sat)</sub>		1.45 2.2	Vdc
DYNAMIC CHARACTERISTICS		1		ı	

Magnitude of Common Emitter Small-Signal Sho Forward Current Transfer Ratio	ort-Circuit				
$I_C = 500$ mAdc, $V_{CE} = 5$ Vdc, $f = 10$ MHz	2N5151 2N5153	$ h_{\mathrm{fe}} $	6 7		
Common-Emitter Small-Signal Short-Circuit. Forward-Current Transfer Ratio					
$I_C = 100$ mAdc, $V_{CE} = 5$ Vdc, $f = 1$ kHz	2N5151 2N5153	$h_{\mathrm{fe}}$	20 50		
Output Capacitance $V_{CB} = 10Vdc$ , $I_E = 0$ , $f = 1.0MHz$		C <sub>obo</sub>		250	pF

### **SWITCHING CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
$\begin{aligned} & \text{Turn-On Time} \\ & I_C = 5 \text{Adc}, I_{B1} = 500 \text{mAdc} \\ & I_{B2} = -500 \text{mAdc} \\ & R_L = 6 \Omega \\ & V_{BE(OFF)} = 3.7 V dc \end{aligned}$	t <sub>on</sub>		0.5	μs
$\begin{aligned} & \text{Turn-Off Time} \\ & I_C = 5 \text{Adc, } I_{B1} = 500 \text{mAdc} \\ & I_{B2} = -500 \text{mAdc} \\ & R_L = 6 \Omega \\ & V_{BE(OFF)} = 3.7 V \text{dc} \end{aligned}$	${ m t_{off}}$		1.5	μs

T4-LDS-0132 Rev. 1 (091476) Page 2 of 4



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#### **SWITCHING CHARACTERISTICS (cont.)**

Parameters / Tes	ters / Test Conditions Symbol Min. Max.		Max.	Unit	
Storage Time	$I_{C} = 5Adc, I_{B1} = 500mAdc$ $I_{B2} = -500mAdc$	t <sub>s</sub>		1.4	μs
Fall Time	$R_{L} = 6\Omega$ $V_{BE(OFF)} = 3.7Vdc$	$t_{\mathrm{f}}$		0.5	μs

#### SAFE OPERATING AREA

#### **DC** Tests

 $T_C = +25$ °C, 1 Cycle,  $t_P = 1.0$ s

Test 1

 $V_{CE} = 5.0 Vdc$ ,  $I_C = 2.0 Adc$ 

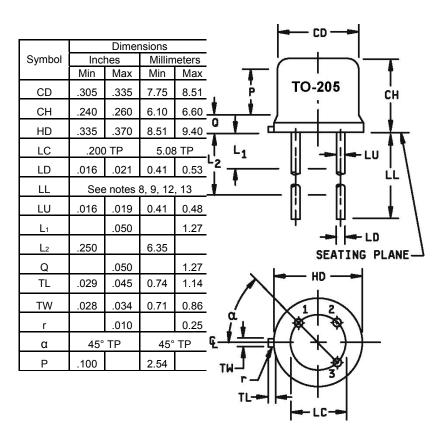
Test 2

 $V_{CE} = 32Vdc, I_C = 310mAdc$ 

Test 3

 $V_{CE} = 80 Vdc$ ,  $I_C = 14.5 mAdc$ 

## FIGURE 1 (TO-5, TO-39) PACKAGE DIMENSIONS



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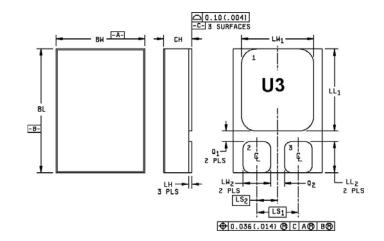
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#### NOTES:

- 1 Dimensions are in inches.
- 2 Millimeters are given for general information only.
- 3 Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 4 TL measured from maximum HD.
- 5 Outline in this zone is not controlled.
- 6 CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 7 Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within.007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- 8 LU applied between L1 and L2. LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 9 All three leads.
- 10 The collector shall be electrically and mechanically connected to the case.
- 11 r (radius) applies to both inside corners of tab.
- 12 In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
- 13 For transistor types 2N5151 and 2N5153, LL is .5 inch (13 mm) minimum, and .75 inch (19 mm) maximum.
- 14 For transistor types 2N5151L and 2N5153L, LL is 1.5 inch (38 mm) minimum and 1.75 inch (44.4 mm) maximum.
- 15 Lead designation, depending on device type, shall be as follows: lead numbering; lead 1 = emitter, lead 2 = base, and lead 3 = collector.

# FIGURE 2 (U3) PACKAGE DIMMENSIONS

Symbol Dimensions					
Cymbol	Inch	nes	Millime	eters	
	Min	Max	Min	Max	
BL	.395	.405	10.04	10.28	
BW	.291	.301	7.40	7.64	
CH	.1085	.1205	2.76	3.06	
LH	.010	.020	0.25	0.51	
LL1	.220	.230	5.59	5.84	
LL2	.115	.125	2.93	3.17	
LS1	.150 BSC		3.81 BSC		
LS2	.075 BSC		1.91 BSC		
LW1	.281	.291	7.14	7.39	
LW2	.090	.100	2.29	2.54	
Q1	.030	_	0.762		
Q2	.030		0.762		



#### NOTES:

- 1 Dimensions are in inches.
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- 3 Terminal 1 collector, terminal 2 base, terminal 3 emitter

T4-LDS-0132 Rev. 1 (091476)